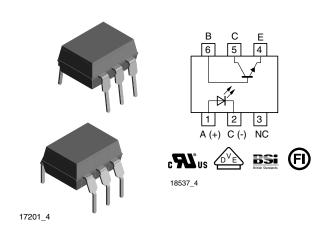


Vishay Semiconductors

### **Optocoupler, Phototransistor Output**



### **DESCRIPTION**

The 4N25V, 4N25GV, 4N35V, 4N35GV series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

### **VDE STANDARDS**

These couplers perform safety functions according to the following equipment standards:

### **DIN EN 60747-5-5 (VDE 0884)**

Optocoupler for electrical safety requirements

#### IEC 60950

Office machines (applied for reinforced isolation for mains voltage  $\leq 400 \ V_{RMS})$ 

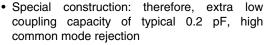
### **VDE 0804**

Telecommunication apparatus and data processing

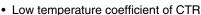
### IEC 60065

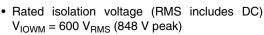
Safety for mains-operated electronic and related household apparatus

### **FEATURES**











Rated recurring peak voltage (repetitive)
 V<sub>IORM</sub> = 600 V<sub>RMS</sub>

• Thickness through insulation ≥ 0.4 mm

- Creepage current resistance according to VDE 0303/ IEC 60112 comparative tracking index: CTI ≥ 275
- Rated impulse voltage (transient overvoltage)
   V<sub>IOTM</sub> = 6 kV peak
- Isolation test voltage (partial discharge test voltage)  $V_{pd} = 1.6 \text{ kV}$
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

### **APPLICATIONS**

- Switch-mode power supplies
- · Line receiver
- Computer peripheral interface
- · Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
  - for appl. class I IV at mains voltage  $\leq$  300 V
  - for appl. class I III at mains voltage ≤ 600 V according to DIN EN 60747-5-5

### **AGENCY APPROVALS**

- UL1577, file no. E52744, double protection
- BSI: BS EN 41003, BS EN 60065 (BS 415), pending
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO (SETI): EN 60950, certificate no. FI25155

ORDER INFORMATION (1)	
PART	REMARKS
4N25GV	CTR > 20 % wide lead spacing, DIP-6
4N35GV	CTR > 100 % wide lead spacing, DIP-6
4N25V	CTR > 20 %, DIP-6
4N35V	CTR > 100 %, DIP-6

#### Note

(1) G = leadform 10.16 mm; G is not marked on the body.

## 4N25V, 4N25GV, 4N35V, 4N35GV

## Vishay Semiconductors Optocoupler, Phototransistor Output



ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT	•						
Reverse voltage		$V_{R}$	5	V			
Forward current		I <sub>F</sub>	60	mA			
Forward surge current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	3	Α			
Power dissipation		P <sub>diss</sub>	70	mW			
Junction temperature		T <sub>j</sub>	125	°C			
OUTPUT	•						
Collector emitter voltage		V <sub>CEO</sub>	32	V			
Emitter collector voltage		V <sub>ECO</sub>	7	V			
Collector current		Ic	50	mA			
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA			
Power dissipation		P <sub>diss</sub>	70	mW			
Junction temperature		T <sub>j</sub>	125	°C			
COUPLER							
Isolation test voltage (RMS)		V <sub>ISO</sub>	5000	V <sub>RMS</sub>			
Total power dissipation		P <sub>tot</sub>	200	mW			
Ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C			
Storage temperature range		T <sub>stg</sub>	- 55 to + 125	°C			
Soldering temperature (2)	2 mm from case, t ≤ 10 s	T <sub>sld</sub>	260	°C			

#### **Notes**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

<sup>(2)</sup> Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS (1)								
PARAMETER	TEST CONDITION	MAX.	UNIT					
INPUT								
Forward voltage	I <sub>F</sub> = 50 mA	V <sub>F</sub>		1.2	1.4	V		
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz	C <sub>j</sub>		50		pF		
OUTPUT								
Collector emitter voltage	I <sub>C</sub> = 1 mA	V <sub>CEO</sub>	32			V		
Emitter collector voltage	I <sub>E</sub> = 100 μA	V <sub>ECO</sub>	7			V		
Collector emitter leakage current	$V_{CE} = 10 \text{ V}, I_F = 0,$ $T_{amb} = 100 ^{\circ}\text{C}$	I <sub>CEO</sub>			50	nA		
	V <sub>CE</sub> = 30 V, I <sub>F</sub> = 0, T <sub>amb</sub> = 100 °C	I <sub>CEO</sub>			500	nA		
COUPLER								
Collector emitter saturation voltage	$I_F = 50 \text{ mA}, I_C = 2 \text{ mA}$	V <sub>CEsat</sub>			0.3	V		
Cut-off frequency	$V_{CE}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	f <sub>c</sub>		110		kHz		
Coupling capacitance	f = 1 MHz	C <sub>k</sub>		1		pF		

### Note

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

 $<sup>^{(1)}</sup>$  T<sub>amb</sub> = 25  $^{\circ}$ C, unless otherwise specified.

<sup>(1)</sup> T<sub>amb</sub> = 25 °C, unless otherwise specified.



# Optocoupler, Phototransistor Output Vishay Semiconductors

CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
		4N25V	CTR	20	100		%	
I <sub>C</sub> /I <sub>F</sub>	V = 10 V   = 10 mA	4N25GV			7/0			
	$V_{CE} = 10 \text{ V}, I_F = 10 \text{ mA}$	4N35V	CTR	100	150		%	
		4N35GV	CTR	100	150			
	$V_{CE} = 10 \text{ V}, I_F = 10 \text{ mA},$	4N35V	CTR	40			%	
	$V_{CE} = 10 \text{ V}, I_F = 10 \text{ mA}, T_{amb} = 100 \text{ °C}$	4N35GV	CTR	40			/0	

MAXIMUM SAFETY RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT							
Forward current		I <sub>F</sub>			130	mA	
OUTPUT							
Power dissipation		P <sub>diss</sub>			265	mW	
COUPLER							
Rated impulse voltage		V <sub>IOTM</sub>			6	kV	
Safety temperature		T <sub>si</sub>			150	°C	

### Note

<sup>(1)</sup> According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t <sub>test</sub> = 1 s	V <sub>pd</sub>	1600			V	
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$	V <sub>IOTM</sub>	6000			V	
	(see figure 2)	$V_{pd}$	1400			V	
Insulation resistance	V <sub>IO</sub> = 500 V	R <sub>IO</sub>	10 <sup>12</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	10 <sup>11</sup>			Ω	
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 150 °C (construction test only)	R <sub>IO</sub>	10 <sup>9</sup>			Ω	

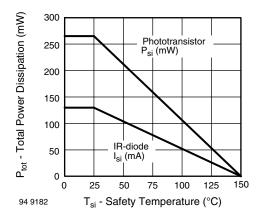


Fig. 1 - Derating Diagram

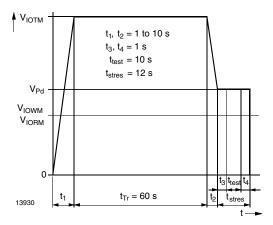


Fig. 2 - Test Pulse Diagram for Sample Test according to DIN EN 60747-; IEC 60747

## 4N25V, 4N25GV, 4N35V, 4N35GV

# Vishay Semiconductors Optocoupler, Phototransistor Output



SWITCHING CHARACTERISTICS								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega,$	4N25V 4N25GV	t <sub>d</sub>		4		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>d</sub>		2.5		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega,$	4N25V 4N25GV	t <sub>r</sub>		7		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>r</sub>		3		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega,$	4N25V 4N25GV	t <sub>f</sub>		6.7		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>f</sub>		4.2		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 5 \text{mA}, R_L = 100 \Omega,$	4N25V 4N25GV	t <sub>s</sub>		0.3		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>s</sub>		0.3		μs	
Turn-on time	$V_S$ = 5 V, $I_C$ = 5 mA, $R_L$ = 100 $\Omega$ ,	4N25V 4N25GV	t <sub>on</sub>		11		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>on</sub>			10	μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega,$	4N25V 4N25GV	t <sub>off</sub>		7		μs	
(see figure 3)	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega,$	4N35V 4N35GV	t <sub>off</sub>			10	μs	
Turn-on time	V - 5 V L - 10 mA B - 1 kO	4N25V 4N25GV	t <sub>on</sub>		25		μs	
(see figure 4)	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$	4N35V 4N35GV	t <sub>on</sub>		9		μs	
Turn-off time	V = 5 V I = 10 mA B = 1 kG	4N25V 4N25GV	t <sub>off</sub>		42.5		μs	
(see figure 4)	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega,$	4N35V 4N35GV	t <sub>off</sub>		25		μs	

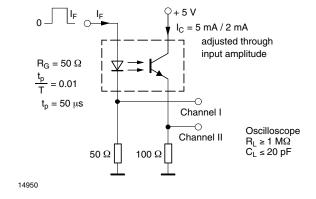


Fig. 3 - Test circuit, Non-Saturated Operation

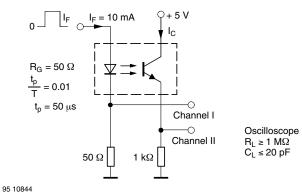


Fig. 4 - Test Circuit, Saturated Operation



## Optocoupler, Phototransistor Output Vishay Semiconductors

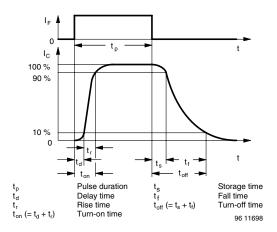


Fig. 5 - Switching Times

### **TYPICAL CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified

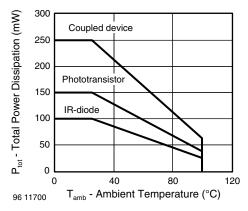


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

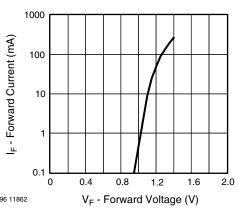


Fig. 7 - Forward Current vs. Forward Voltage

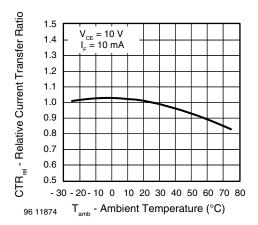


Fig. 8 - Relative Current Transfer Ratio vs.
Ambient Temperature

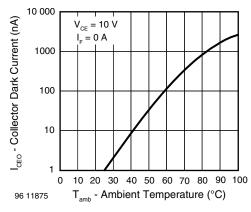


Fig. 9 - Collector Dark Current vs. Ambient Temperature

## Vishay Semiconductors Optocoupler, Phototransistor Output



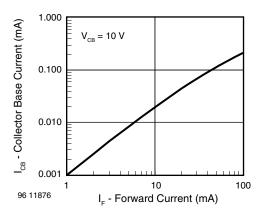


Fig. 10 - Collector Base Current vs. Forward Current

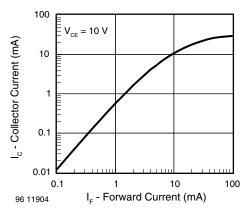


Fig. 11 - Collector Current vs. Forward Current

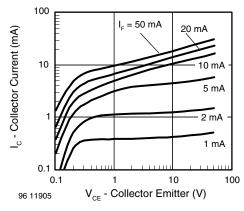


Fig. 12 - Collector Current vs. Collector Emitter Voltage

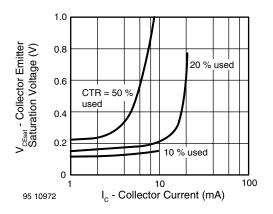


Fig. 13 - Collector Emitter Saturation Voltage vs. Collector Current

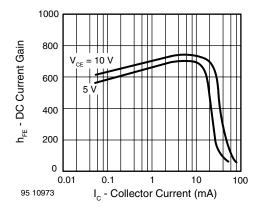


Fig. 14 - DC Current Gain vs. Collector Current

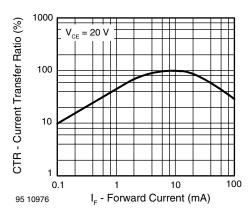


Fig. 15 - Current Transfer Ratio vs. Forward Current



## Optocoupler, Phototransistor Output Vishay Semiconductors

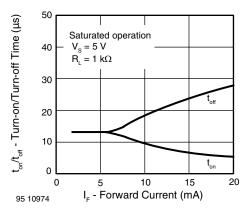


Fig. 16 - Turn-on/off Time vs. Forward Current

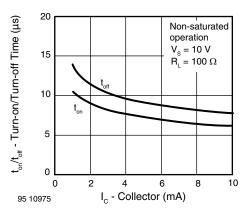
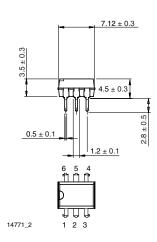
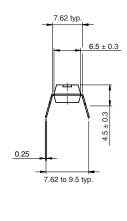


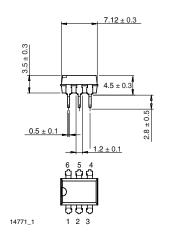
Fig. 17 - Turn-on/off Time vs. Collector Current

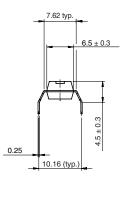
# **PACKAGE DIMENSIONS** in millimeters **DIP-6**





### DIP-6, 400 mil





### **PACKAGE MARKING**



### **Legal Disclaimer Notice**



Vishay

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